

*Spring 2019 Purdue University*

# **ECE 255: L11.2**

# **BJT Circuit Analysis and Design**

(Sedra and Smith, 7<sup>th</sup> Ed., Sec. 6.2)

Mark Lundstrom  
School of ECE  
Purdue University  
West Lafayette, IN USA

Lundstrom: 2019

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# Announcements

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**Exam 1: Thursday, Feb. 7, 6:30 PM, LILY 1105.**

(Weeks -1- 4 topics, semiconductors, diodes, **BJTs**. i.e. HW1-HW4)

**Two practice exams are posted on BlackBoard**

**Professor Janes will conduct a help session for Exam 1 on Thursday, 2/7 at 1:30 PM in ME 1061.**

**Spice 1 project postponed until Monday, Feb. 11**

**Note that there was an error in Lecture 11 Slide 8. Now corrected (and L11 has been split into two parts)**

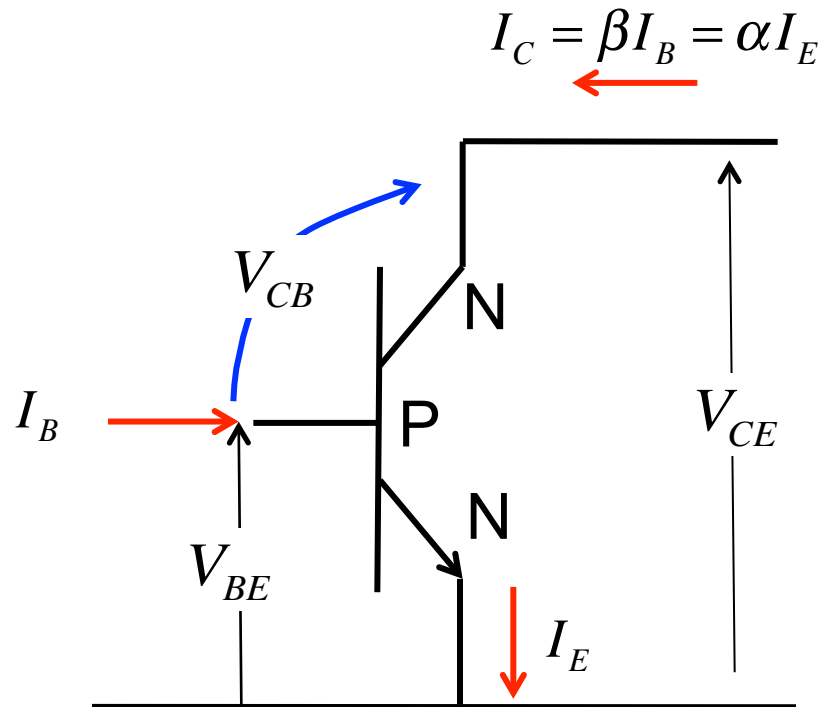
# Announcements

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**We will have class on Friday, Feb. 8.**

**The topic will be MOSFETs. Sedra and Smith 5.1 and 5.2**

# NPN Common emitter (active region)



$$I_C = I_S e^{V_{BE}/V_T} \quad I_B = \frac{I_S}{\beta} e^{V_{BE}/V_T}$$

$$I_C = \beta I_B \quad I_C = \alpha I_E$$

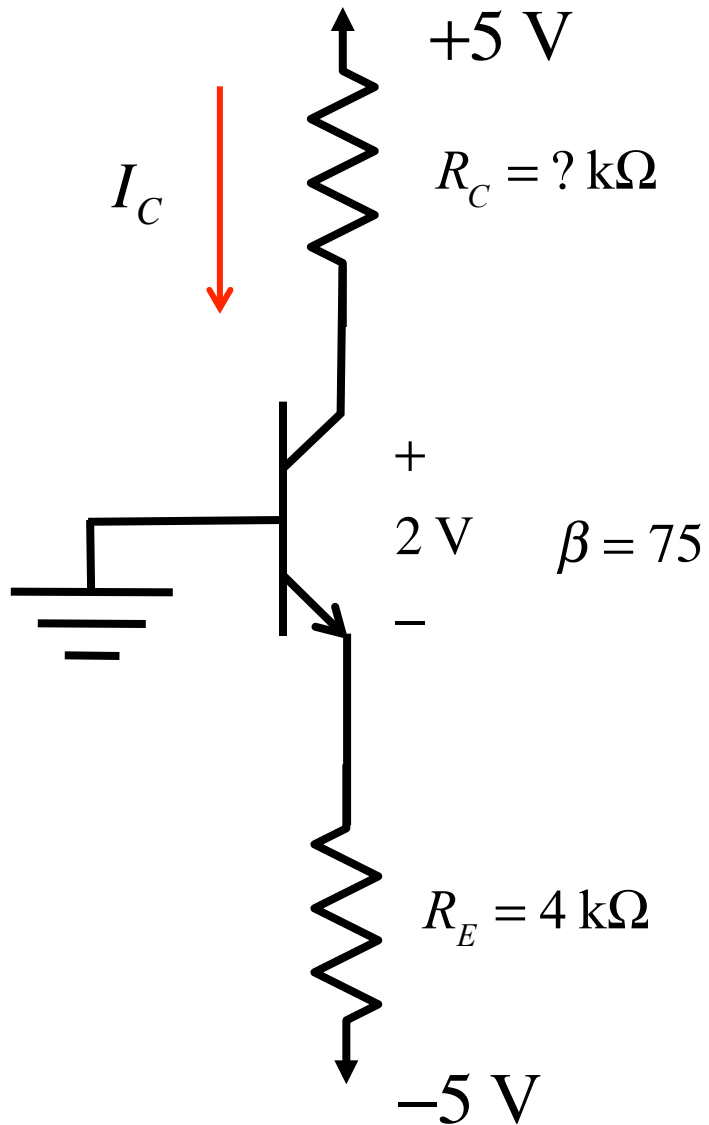
$$\beta = \frac{\alpha}{1 - \alpha} \gg 1 \quad \alpha = \frac{\beta}{\beta + 1} < 1$$

BE: **FB**  $V_{BE} > 0$

BC: **RB**  $V_{CB} = V_{CE} - V_{BE} > 0$

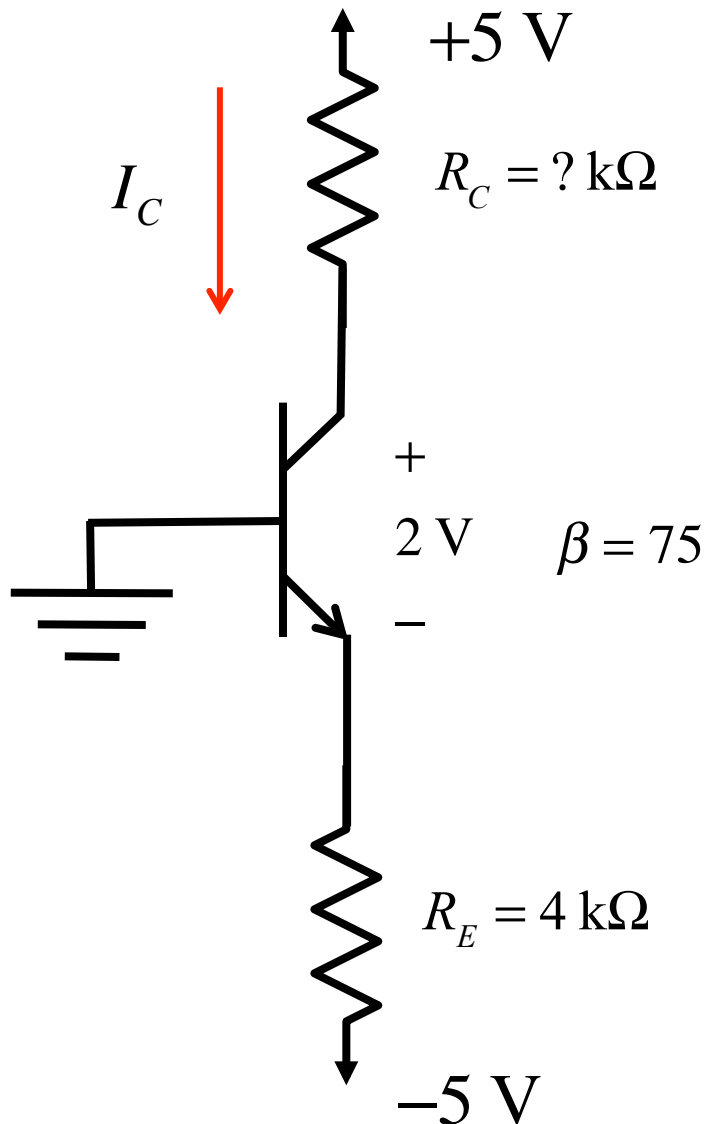
# NPN DC circuit analysis

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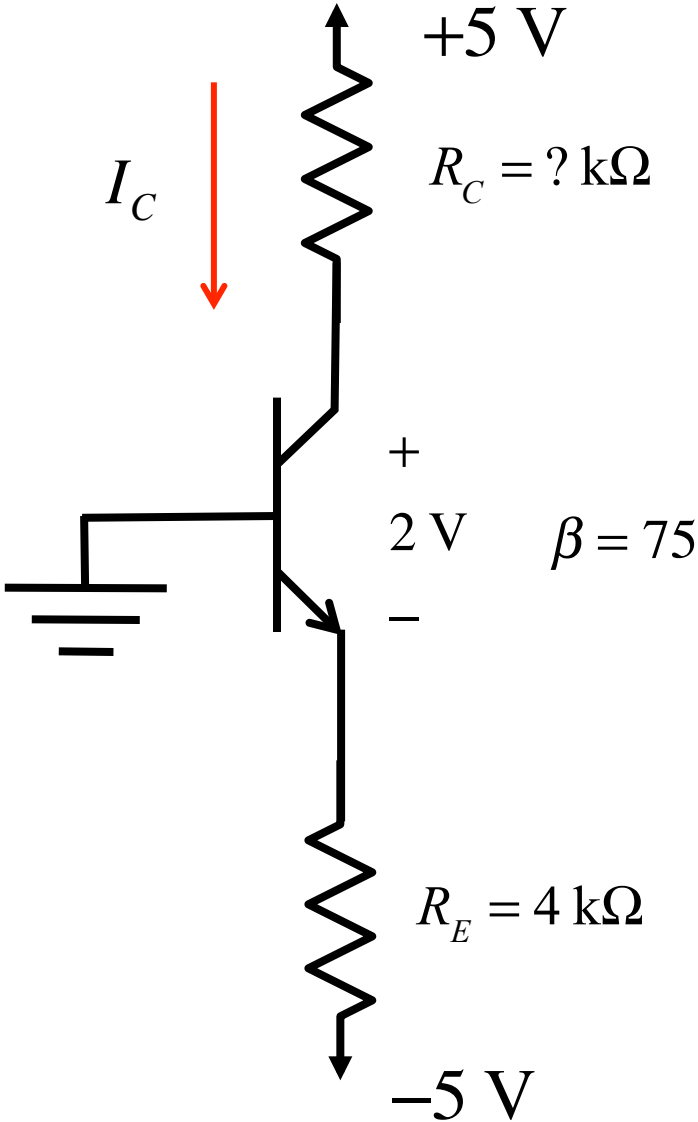
**Find  $I_C$  and  $R_C$**

# DC circuit analysis

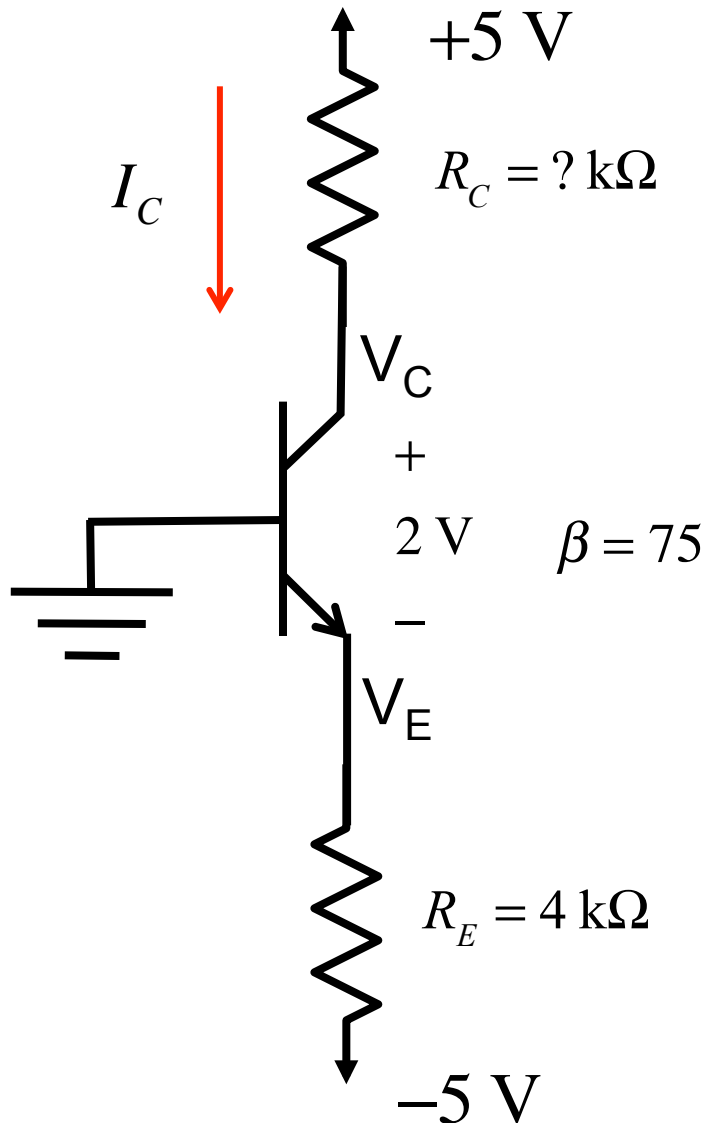


- 1) Assume active region
- 2) Find  $I_E$
- 3) Find  $I_C$
- 4) Find  $V_C$
- 5) Find  $R_C$
- 6) Check: Active region?

# DC circuit analysis



# DC circuit analysis



Circuit:  $V_B = 0\text{V}$

Forward Active:  $V_{BE} = 0.7\text{V}$

$\Rightarrow V_E = -0.7\text{V}$

$I_E = 4.3\text{V}/4\text{k}\Omega = 1.08\text{ mA}$

$I_C = \alpha I_E = 1.07\text{ mA}$

Specified:  $V_{CE} = 2\text{V}$

$V_E = -0.7\text{V} \Rightarrow V_C = 1.3\text{ V}$

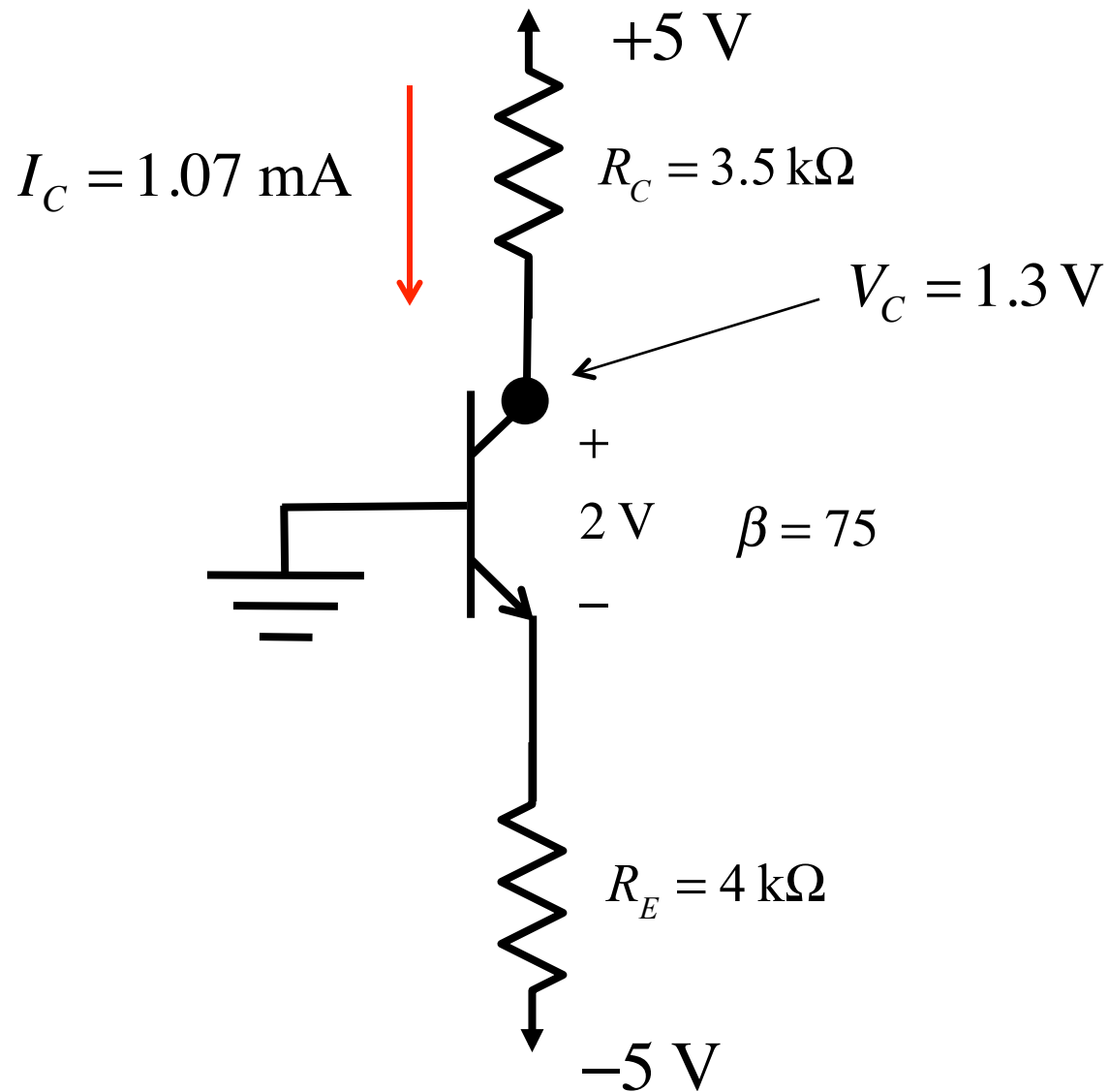
Voltage across  $R_C = 3.7\text{V}$

$R_C = 3.5\text{ k}\Omega$



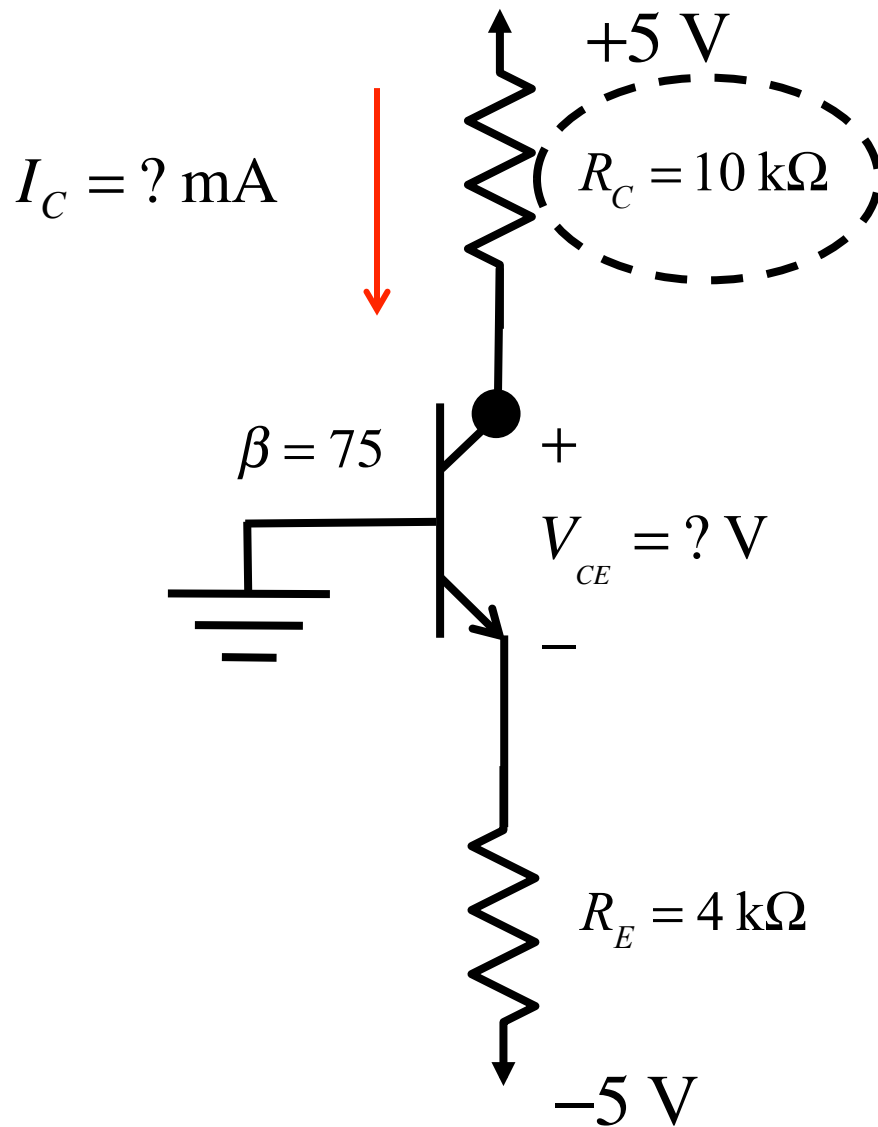
## DC circuit analysis: Result

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Now change the problem

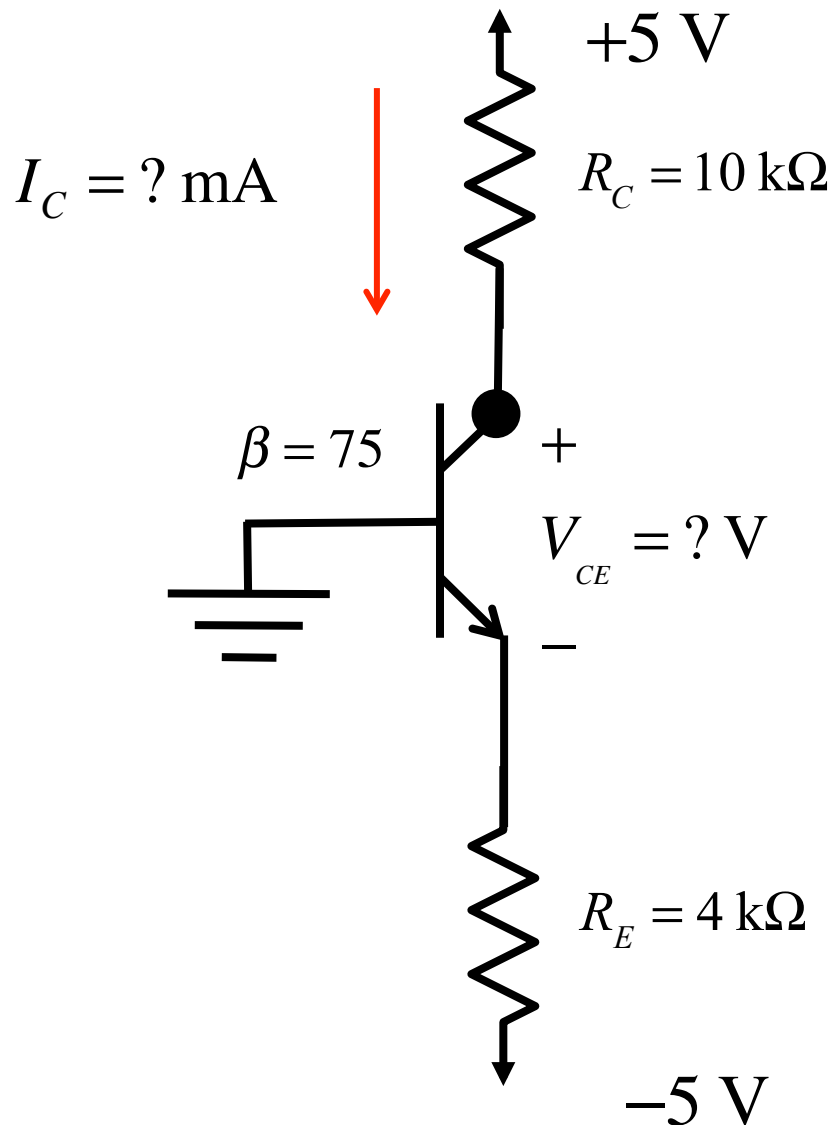
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**Find  $I_C$  and  $V_{CE}$**

## Now change the problem

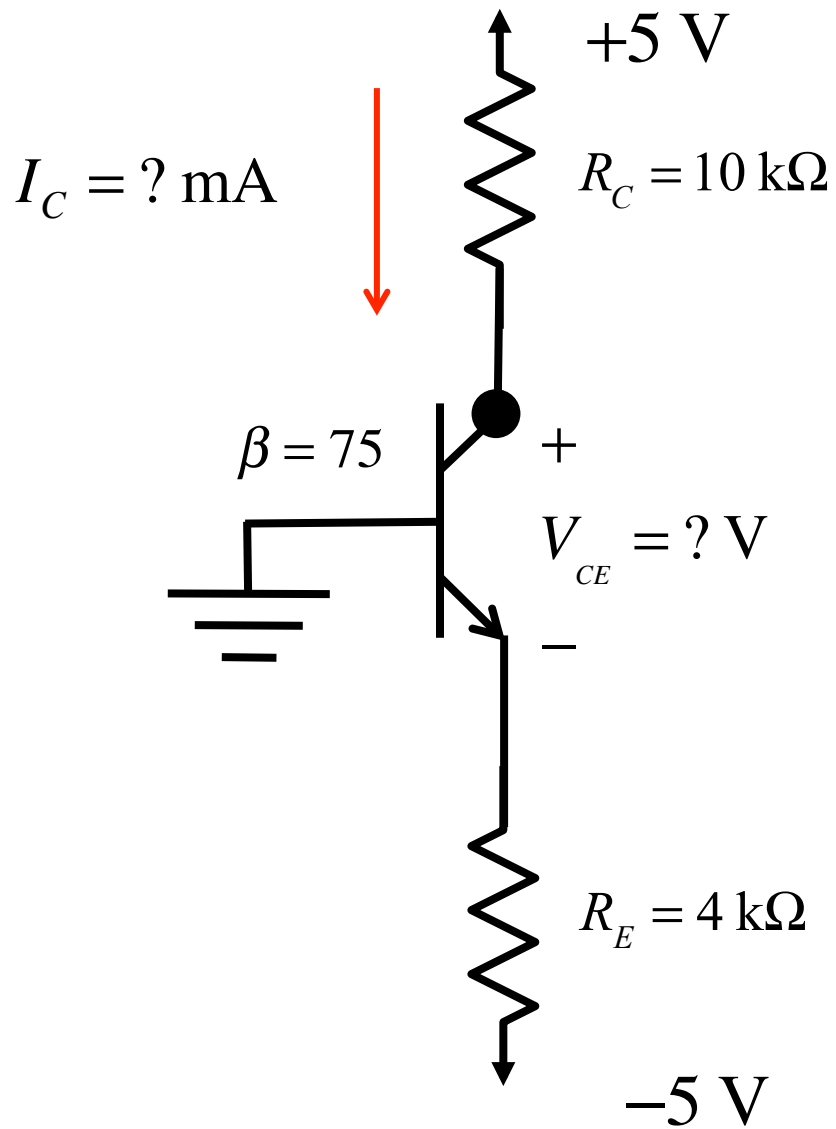
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- 1) Assume active region
- 2) Find  $I_E$
- 3) Find  $I_C$
- 4) Find  $V_C$
- 5) Find  $R_C$
- 6) Check: Active region?

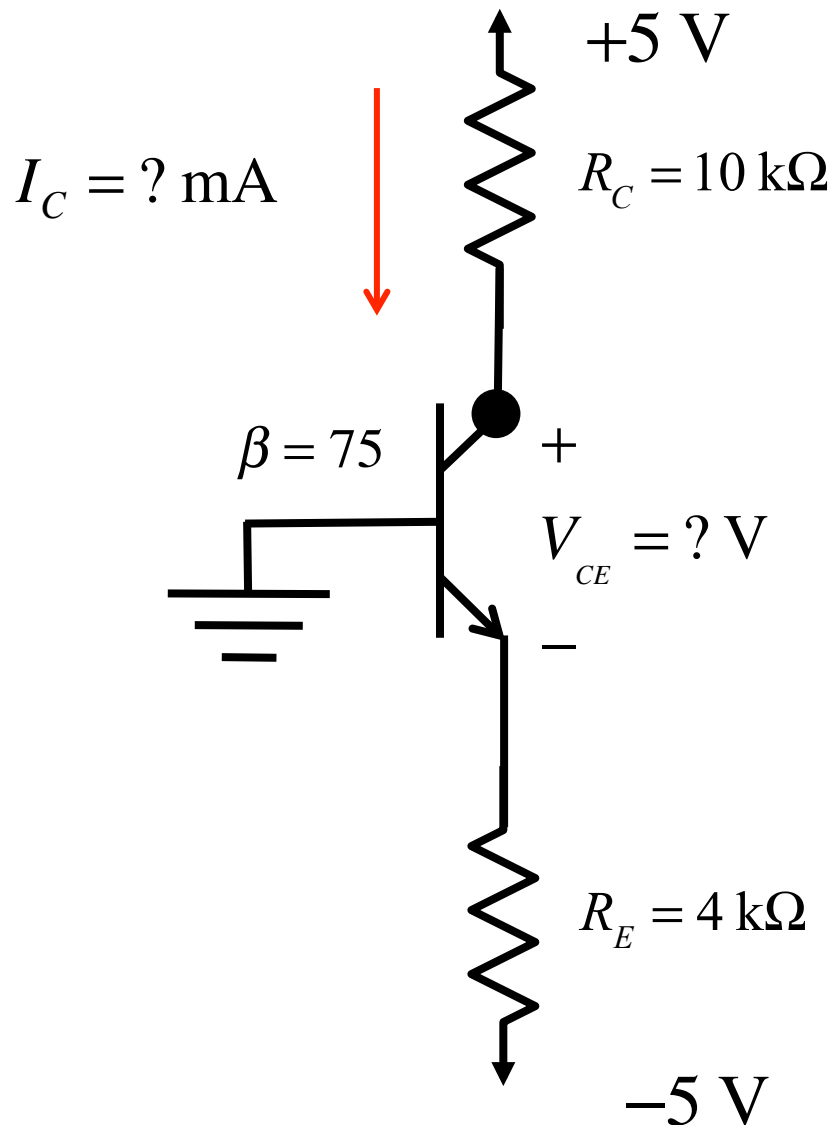
## Now change the problem

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## Now change the problem

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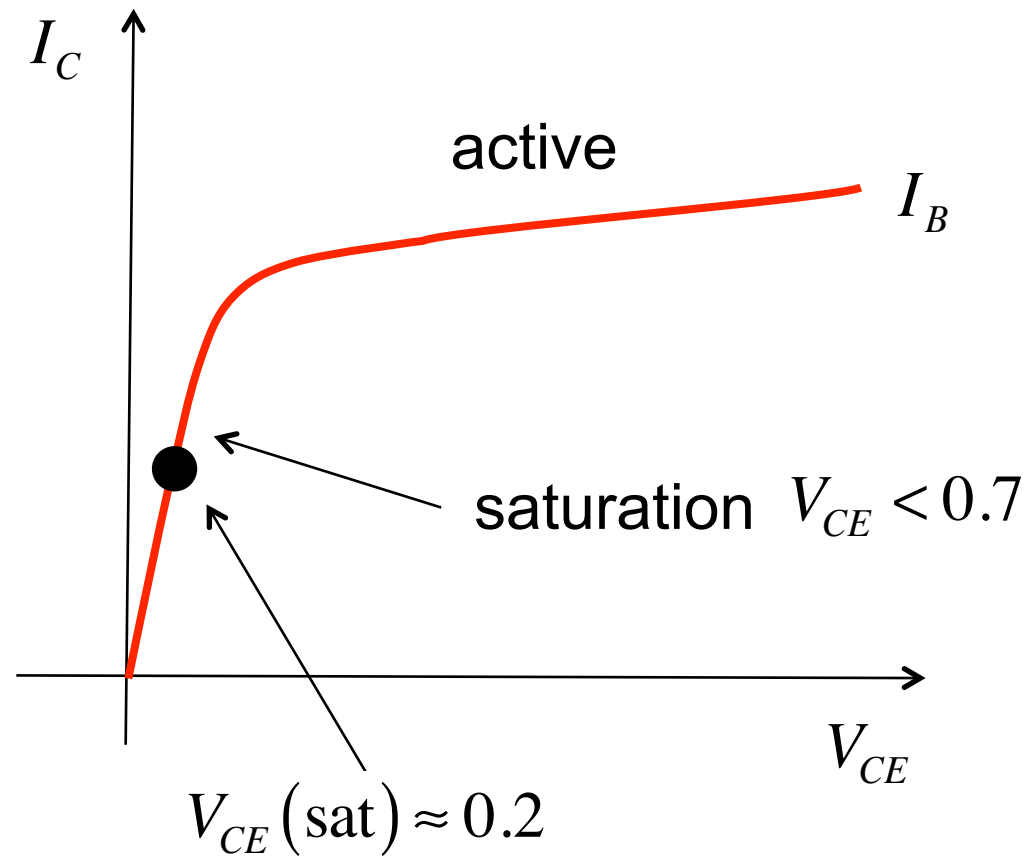
$$I_E = \frac{-0.7 - (-5.0)}{4\text{ k}\Omega} = 1.08\text{ mA}$$

$$I_C = \frac{\beta}{\beta + 1} I_E = 1.07\text{ mA}$$

$$V_C = 5 - 1.07 \times 10 < 0!$$

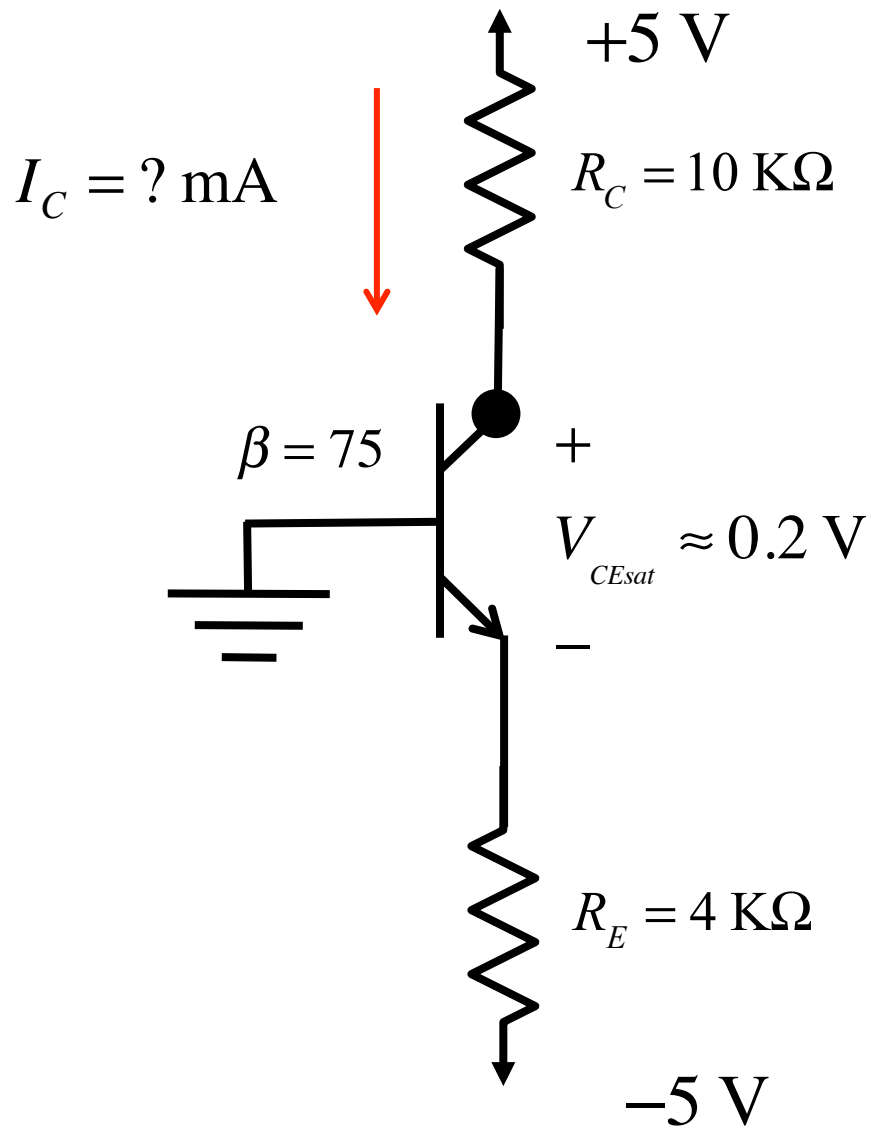
# The transistor is saturated!

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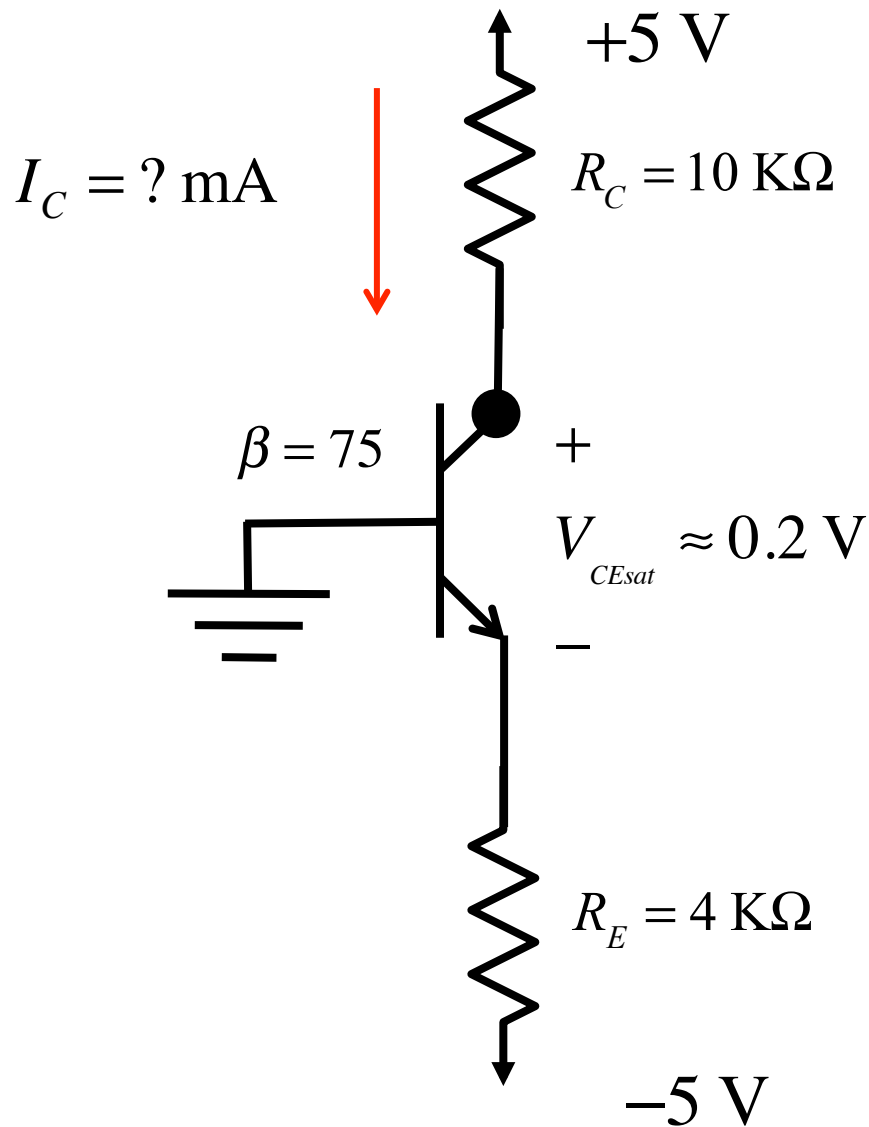


# Saturation analysis

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## Saturation analysis: result



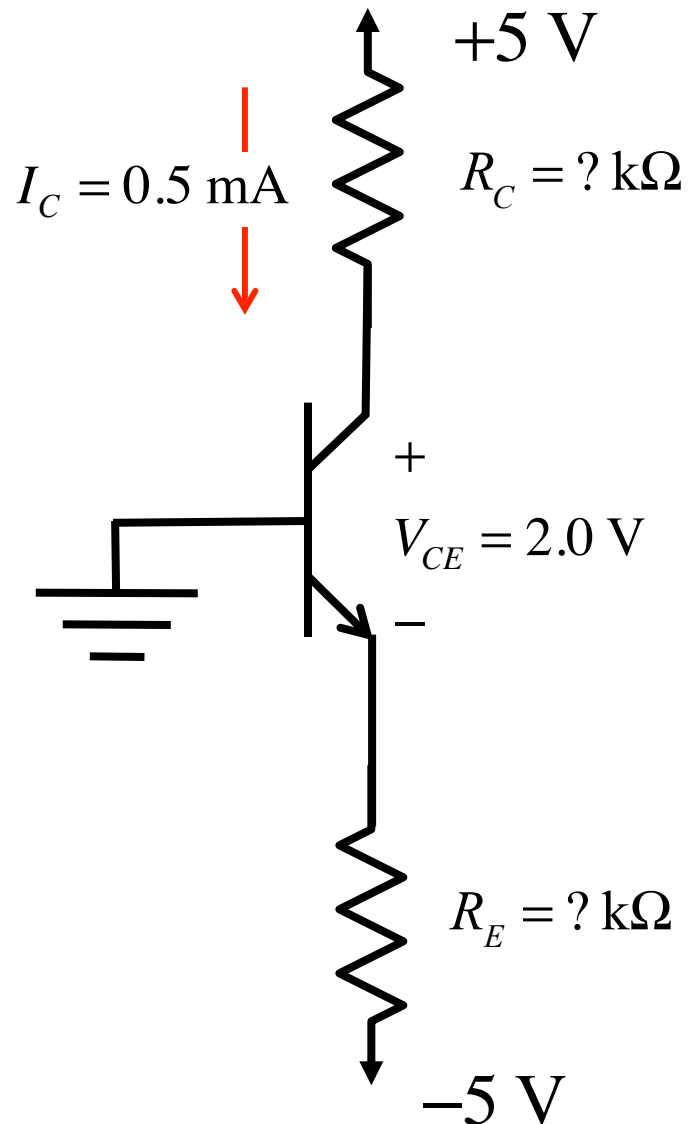
$$I_E = \frac{-0.7 - (-5.0)}{4 \text{ k}\Omega} = 1.08 \text{ mA}$$

$$V_C = -0.7 + 0.2 = -0.5 < 0$$

$$I_C = \frac{5 - (-0.5)}{10 \text{ k}\Omega} = 0.55 \text{ mA}$$



# DC circuit design



Specify  $R_C$  and  $R_E$  so that:

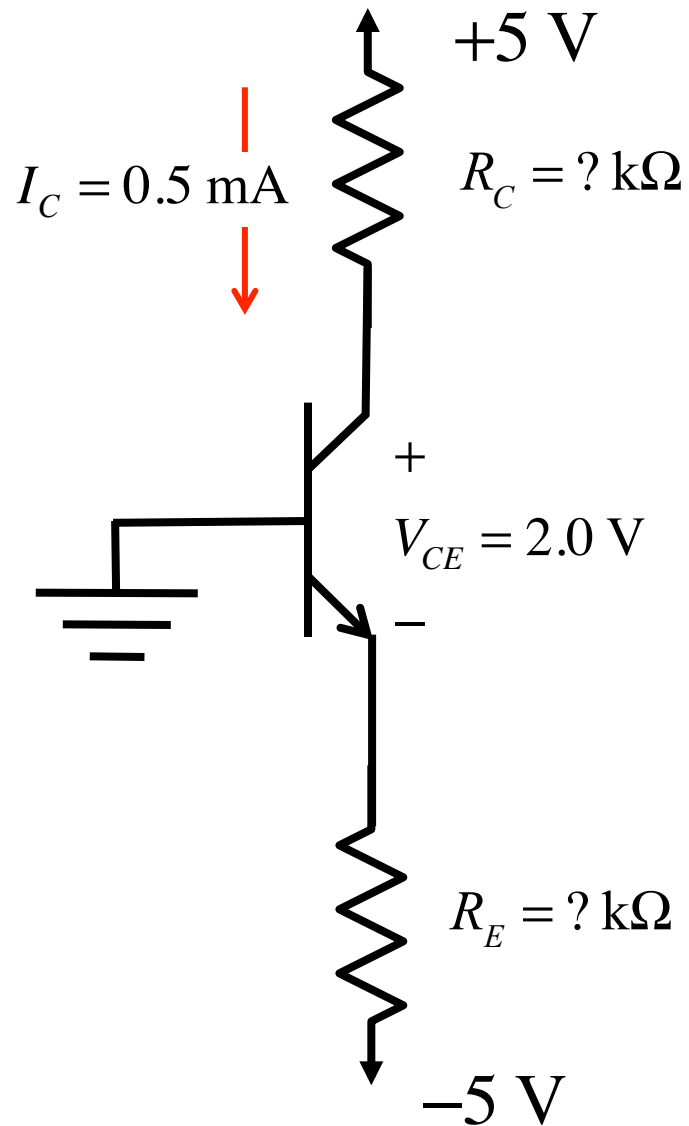
$$I_C \approx 0.5 \text{ mA}$$

$$V_{CE} \approx 2.0 \text{ V}$$

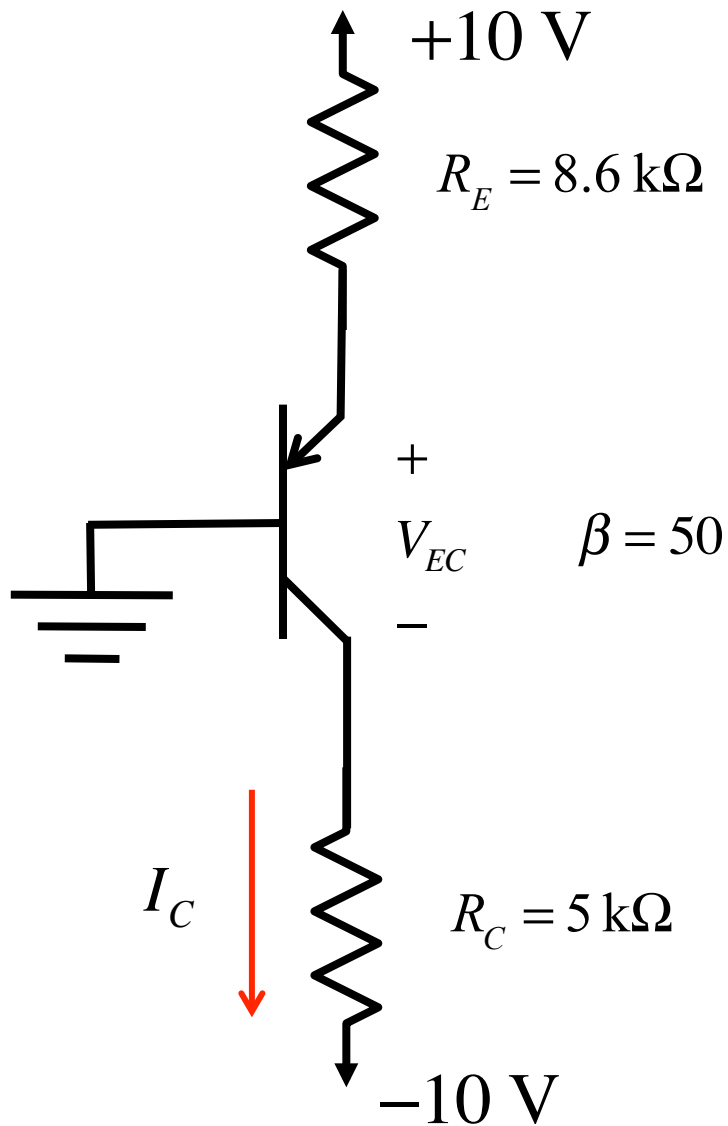
$$\beta = 75$$

# NPN DC circuit design

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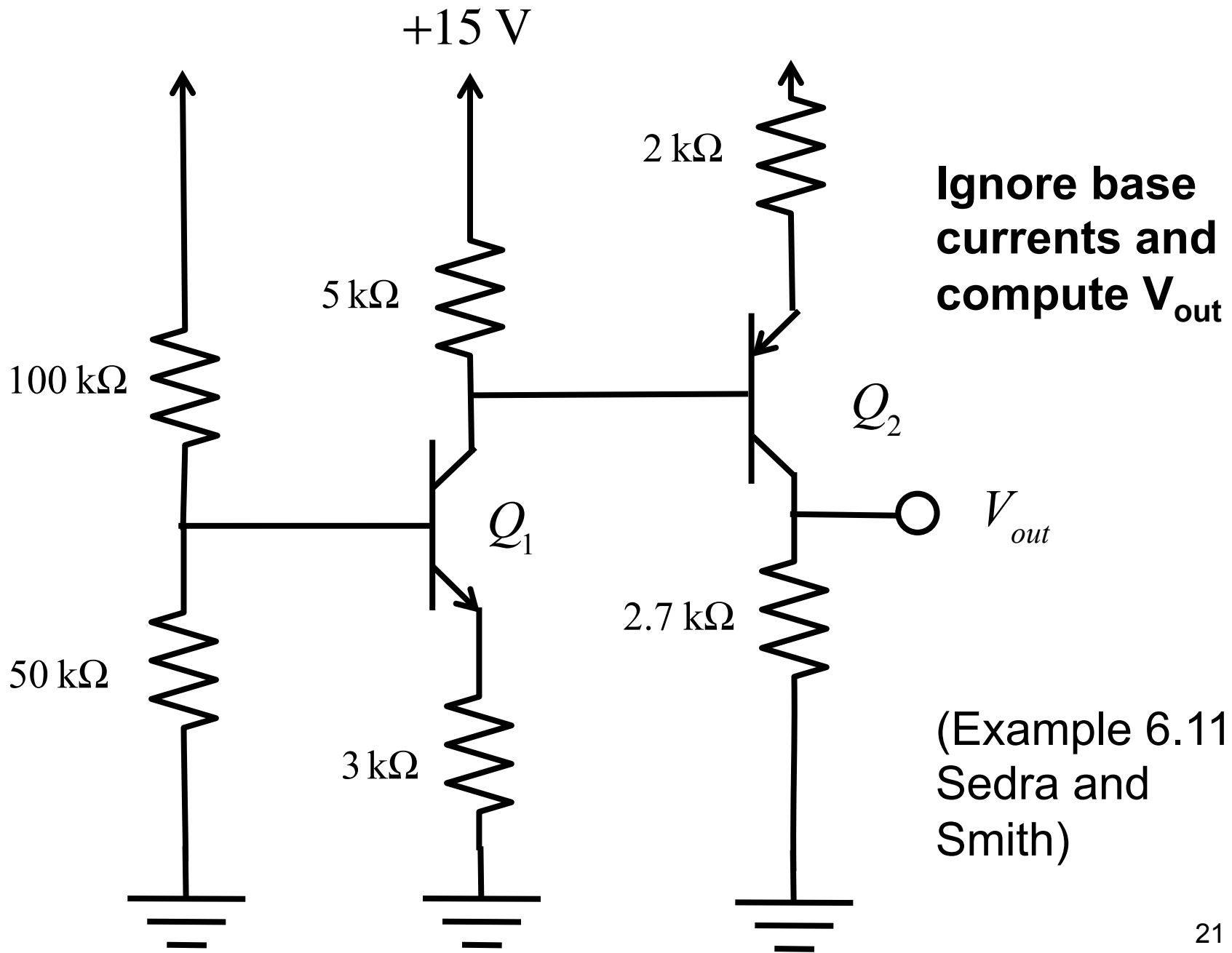
# PNP Circuit Analysis



**Find  $I_C$  and  $V_{EC}$**

# NPN and PNP Circuit Analysis

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# Summary

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In analysis, assume an operating region, do the analysis, then check that the proper operating region was assumed.

Generally, design is “easier” than analysis (but more open).

# BJT Circuit Analysis and Design

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- 1) NPN BJT Circuit Analysis and Design
- 2) PNP Circuits
- 3) NPN and PNP Circuits

